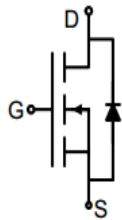
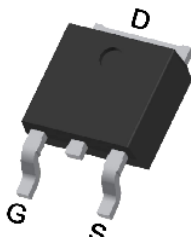


N-Channel Enhancement Mode Power MOSFET

Description The G58N06K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.		 Schematic diagram	
General Features • V_{DS} 60V • I_D (at $V_{GS} = 10V$) 58A • $R_{DS(ON)}$ (at $V_{GS} = 10V$) $< 13m\Omega$ • $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) $< 20m\Omega$ • 100% Avalanche Tested • RoHS Compliant		 TO-252	
Application • Power switch • DC/DC converters			
Device	Package	Marking	Packaging
G58N06K	TO-252	G58N06	2500pcs/Reel

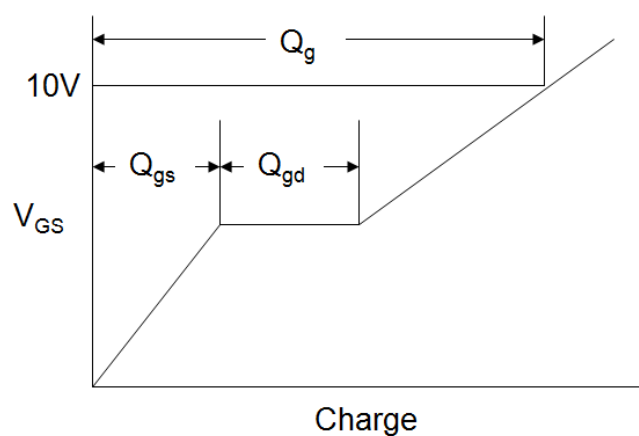
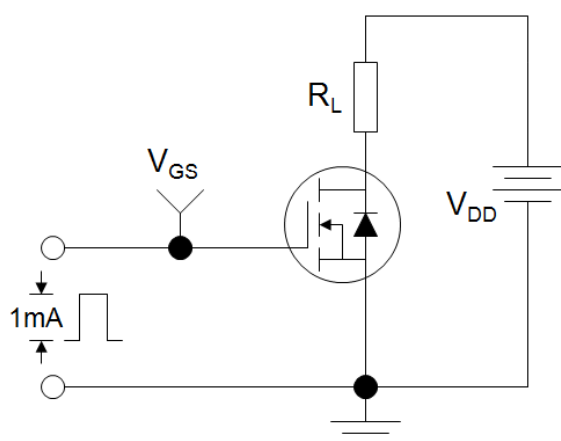
Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	58	A
Pulsed Drain Current (note1)	I_{DM}	120	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	71	W
Single pulse avalanche energy (note3)	E_{AS}	91	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ C$
Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.76	$^\circ C/W$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.8	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 30A	--	10.5	13	mΩ
		V _{GS} = 4.5V, I _D = 25A	--	12.5	20	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	18	--	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	2500	--	pF
Output Capacitance	C _{oss}		--	185	--	
Reverse Transfer Capacitance	C _{rss}		--	80	--	
Total Gate Charge	Q _g	V _{DD} = 30V, I _D = 30A, V _{GS} = 10V	--	36	--	nC
Gate-Source Charge	Q _{gs}		--	10	--	
Gate-Drain Charge	Q _{gd}		--	6.5	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, I _D = 2A, R _G = 3Ω	--	12	--	ns
Turn-on Rise Time	t _r		--	5	--	
Turn-off Delay Time	t _{d(off)}		--	38	--	
Turn-off Fall Time	t _f		--	27	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	58	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 20A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	T _{rr}	I _S = 30A, V _{GS} = 0V di/dt=100A/us	--	35	--	ns
Reverse Recovery Charge	Q _{rr}		--	47	--	nC

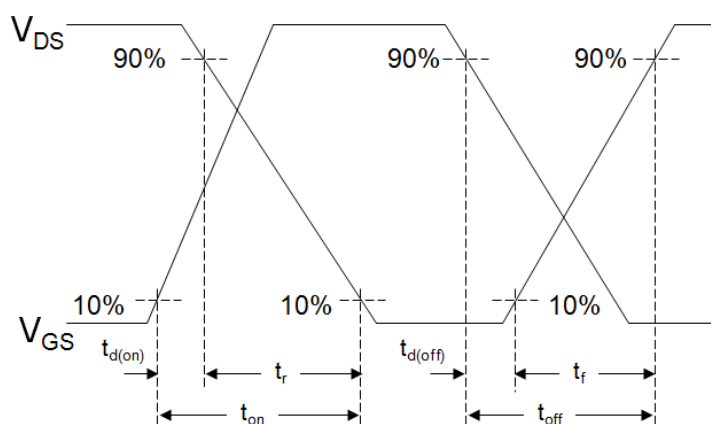
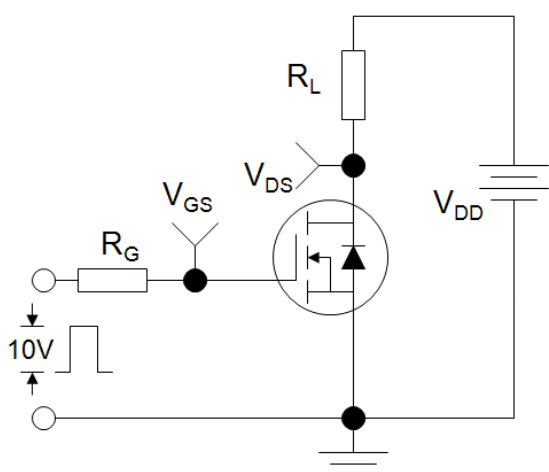
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J=25^\circ\text{C}$, $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$

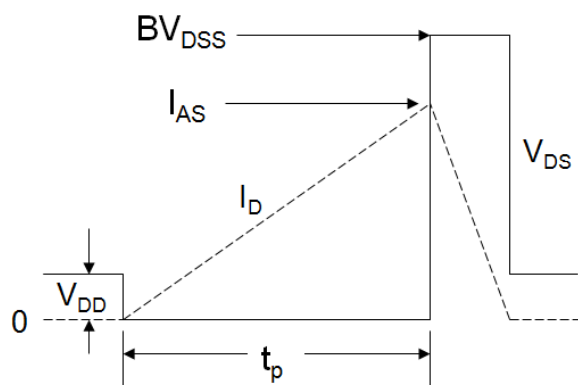
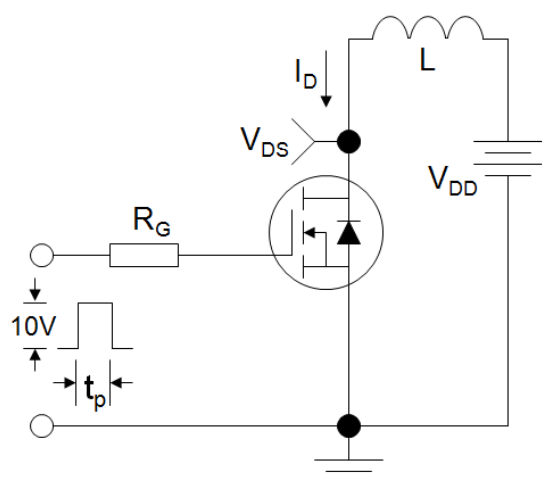
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

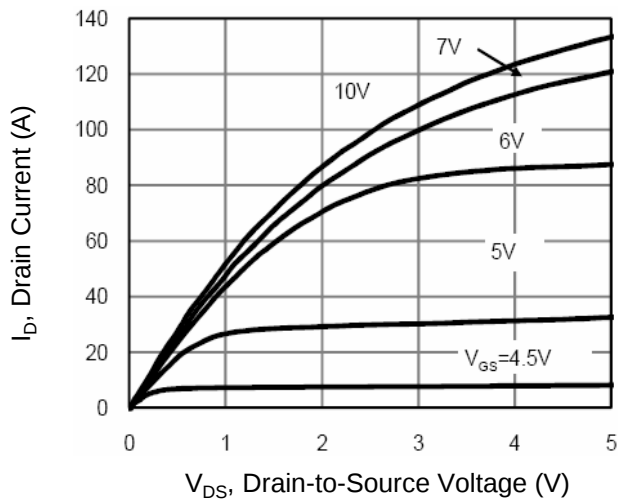


Figure 2. Transfer Characteristics

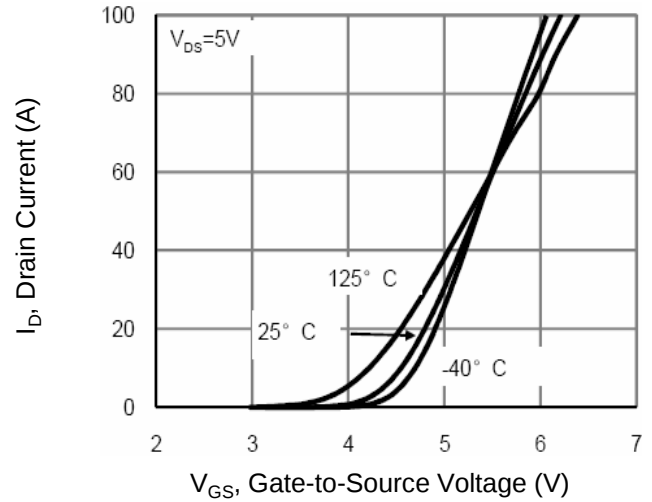


Figure 3. Gate Charge

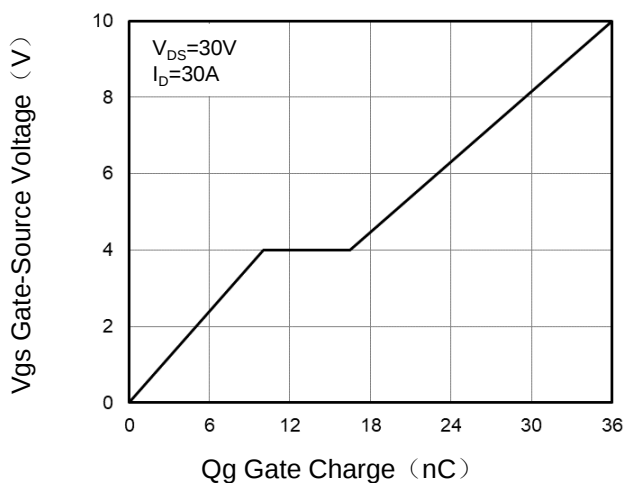


Figure 4. Drain Source On Resistance

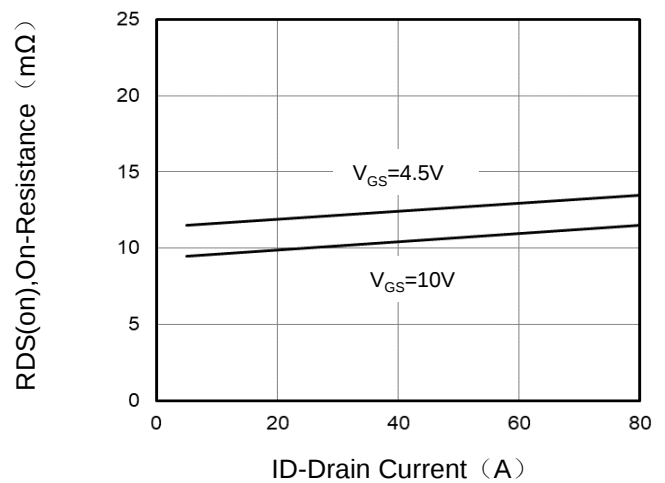


Figure 5. Capacitance

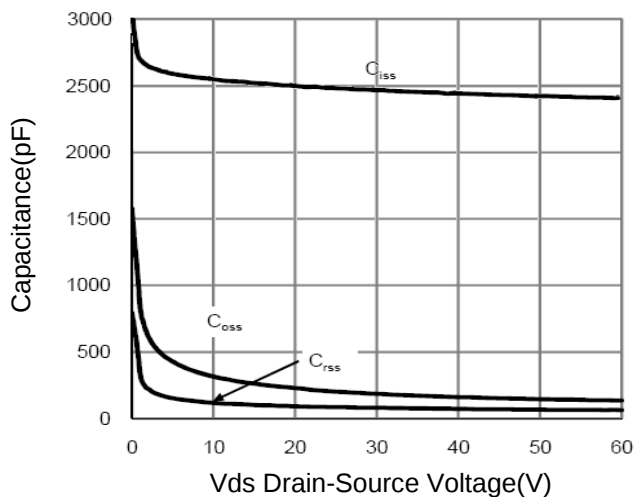
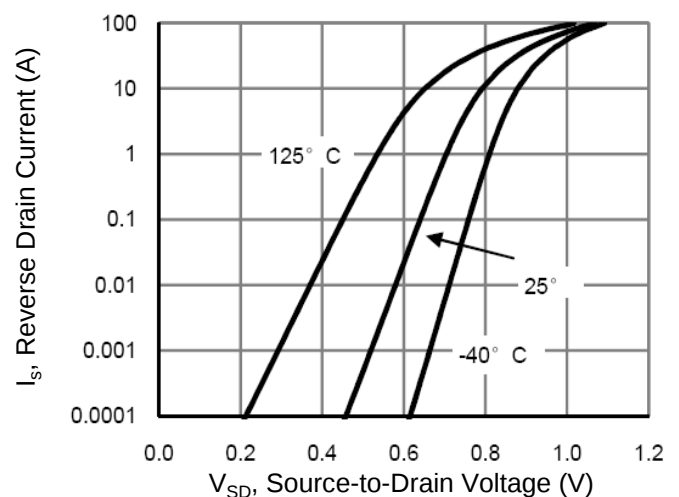


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

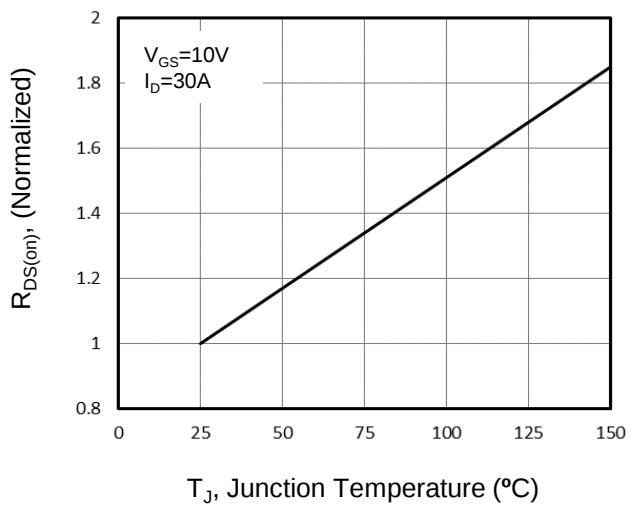


Figure 8. Safe Operation Area

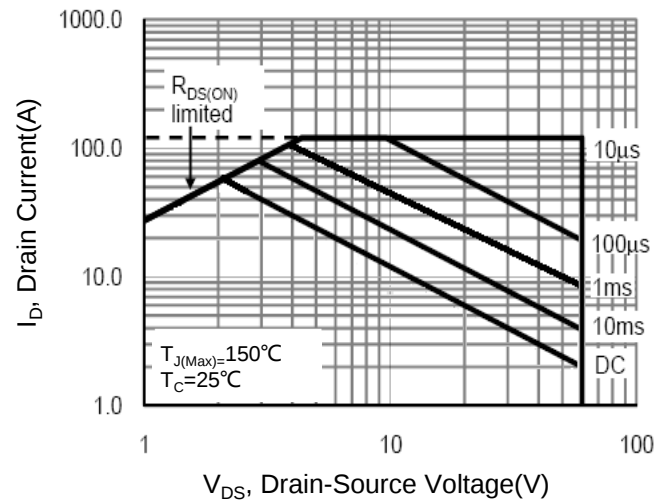
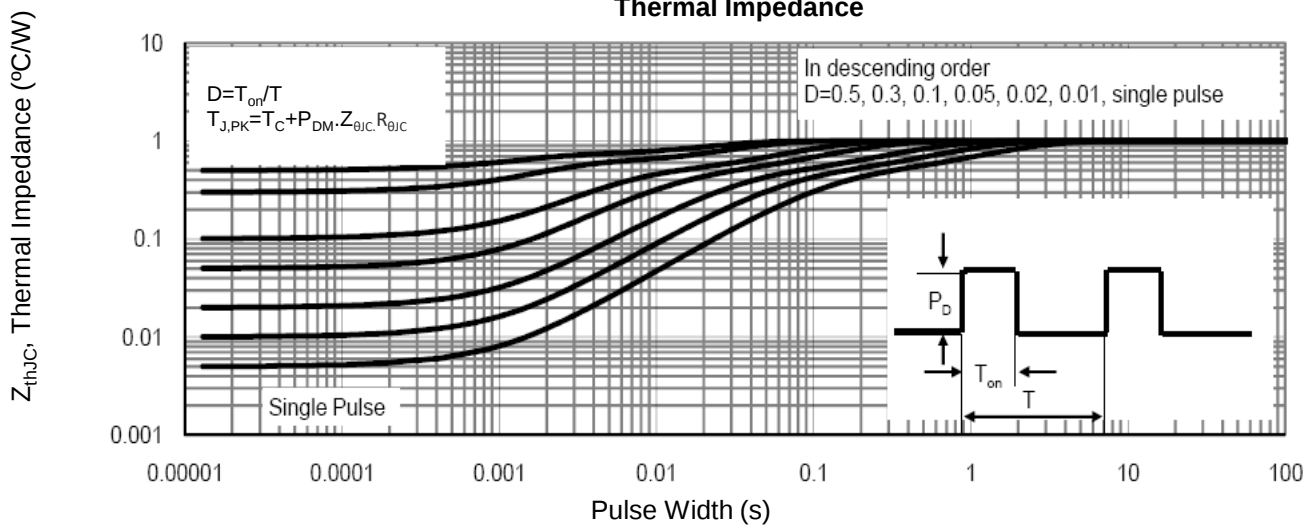
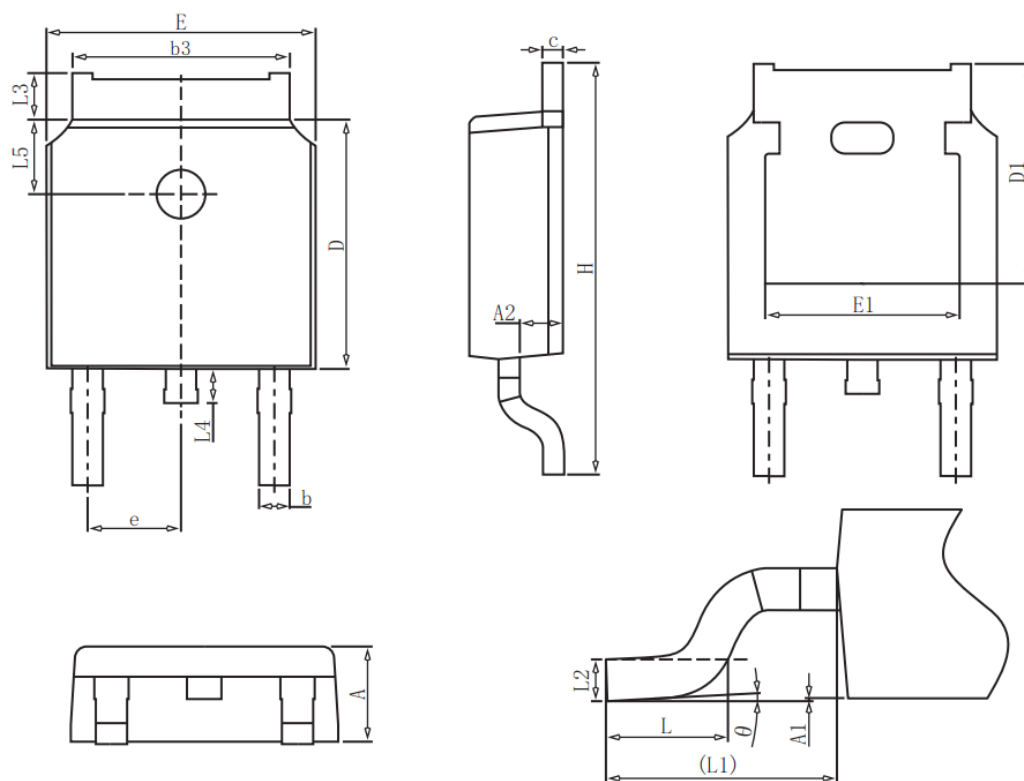


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.2	2.3	2.4
A1	0		0.2
A2	0.97	1.07	1.17
b	0.68	0.78	0.9
b3	5.2	5.33	5.5
c	0.43	0.53	0.63
D	5.98	6.1	6.22
D1	5.30REF		
E	6.4	6.6	6.8
E1	4.63		
e	2.286BSC		
H	9.4	10.1	10.5
L	1.38	1.5	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88		1.28
L4	0.5		1
L5	1.65	1.8	1.95
θ	0°		8°